EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	14	(@ad<"20040921" or @rlad<"20040921") and (second near polysilicon near emitter)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/27 14:42
L5	14	(@ad<"20040921" or @rlad<"20040921") and (transistor bipolar base emitter collector sige silicon germanium dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon gallium argon aluminum concentration first second substrate wafer) and (second near polysilicon near emitter)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/27 13:10
L6	7	("5818153" | "5882976" | "6051873" | "6194280" | "6248650" | "6384469").PN. OR ("6686250"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/27 14:36
L7	1228	(@ad<"20040921" or @rlad<"20040921") and (second with (poly polysilicon) with emitter) not l5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/27 15:22
L8	225	(@ad<"20040921" or @rlad<"20040921") and (second with (poly polysilicon) with emitter) and collector and base and bipolar and (carbon germanium argon) not l5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/27 15:24
L9	408	(@ad<"20040921" or @rlad<"20040921") and 257/198. ccls. and (base emitter collector bipolar sige (silicon near germanium) dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration first second substrate)	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/27 15:42
S1	2	("5656514").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/19 09:07

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S2	2142	(@ad<"20040921" or @rlad<"20040921") and base and emitter and collector and bipolar and (sige or (silicon near germanium)) and (dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration) and (first second) and (substrate wafer silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/19 13:45
S3	1258	(@ad<"20040921" or @rlad<"20040921") and (transistor bipolar).ab. and base and emitter and collector and bipolar and (sige or (silicon near germanium)) and (dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration) and (first second) and (substrate wafer silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/27 13:07
S4	25	(@ad<"20040921" or @rlad<"20040921") and (transistor bipolar).ab. and base and emitter and collector and bipolar and (sige or (silicon near germanium)) and (dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration) and (first second) and (substrate wafer silicon) and "first base" and "second base" and "first emitter" and "second emitter"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 15:49
S7	345	(@ad<"20040921" or @rlad<"20040921") and (transistor bipolar).ab. and base and emitter and collector and bipolar and ("sic" or (silicon near carbon)) and (dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration) and (first second) and (substrate wafer silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/23 10:23

EAST Search History

S9	10	(@ad<"20040921" or @rlad<"20040921") and (transistor bipolar).ab. and base and emitter and collector and bipolar and ("sic" or (silicon near carbon)) and (dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration) and (first second) and (substrate wafer silicon) and "first base" and "second base" and "first emitter" and "second emitter"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/22 15:50
S12	42	(@ad<"20040921" or @rlad<"20040921") and (("4319932" | "4967254" | "5006912" | "5063427" | "5106767" | "5323032" | "5346840" | "5389803").PN. OR ("5656514"). URPN.) and (base emitter collector bipolar sige (silicon near germanium) dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration first second substrate wafer)	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/22 16:18
S18	17	(@ad<"20040921" or @rlad<"20040921") and (("4583106" | "5065209" | "5073810" | "5117271" | "5198375" | "5315151" | "5321301" | "5323032").PN. OR ("5508553"). URPN.) and (base emitter collector bipolar sige (silicon near germanium) dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration first second substrate wafer)	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/23 09:07
S19	11	(@ad<"20040921" or @rlad<"20040921") and (transistor bipolar).ab. and base and emitter and collector and bipolar and ("sic" or (silicon near carbon)) and (dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration) and (first second) and (substrate wafer silicon) and "sic base"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/23 10:24

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S20	2	"6967144"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/23 10:42
S22	19	(@ad<"20040921" or @rlad<"20040921") and (("4985742" | "5010382" | "5122845" | "5326992" | "5378921" | "5408120").PN. OR ("5641975").URPN.) and (base emitter collector bipolar sige (silicon near germanium) dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration first second substrate wafer)	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/23 12:59
S23	403	(@ad<"20040921" or @rlad<"20040921") and 257/198. ccls. and (base emitter collector bipolar sige (silicon near germanium) dope dopant impurity arsenic phosphorus phosphorous boron antimony indium carbon germanium gallium argon aluminum concentration first second substrate wafer)	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/27 15:39